Yan-Feng Lao

List of Publications by Year
in descending order

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42	601	567281 15	610901 24
papers	citations	h-index	g-index

43	43	43	676
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Noise, gain, and capture probability of p-type InAs-GaAs quantum-dot and quantum dot-in-well infrared photodetectors. Journal of Applied Physics, 2017, 121, 244501.	2.5	22
2	GaMnAs for Mid-Wave Infrared Photodetection. IEEE Photonics Technology Letters, 2016, 28, 2261-2264.	2.5	0
3	Infrared photodetector with wavelength extension beyond the spectral limit. Proceedings of SPIE, 2016, , .	0.8	1
4	Mid-infrared photodetectors operating over an extended wavelength range up to 90â€‰â€‰K. Optics Letters, 2016, 41, 285.	3.3	3
5	Tunable hot-carrier photodetector. , 2015, , .		0
6	InAs/GaAs quantum dot and dots-in-well infrared photodetectors based on p -type valence-band intersublevel transitions. Infrared Physics and Technology, 2015, 70, 15-19.	2.9	17
7	Optical study of HgCdTe infrared photodetectors using internal photoemission spectroscopy. Applied Physics Letters, 2014, 104, .	3.3	5
8	Band-offset non-commutativity of GaAs/AlGaAs interfaces probed by internal photoemission spectroscopy. Applied Physics Letters, 2014, 105, 171603.	3.3	6
9	Study of valence-band intersublevel transitions in InAs/GaAs quantum dots-in-well infrared photodetectors. Applied Physics Letters, 2014, 104, .	3.3	11
10	Tunable hot-carrier photodetection beyond the bandgap spectral limit. Nature Photonics, 2014, 8, 412-418.	31.4	66
11	Wavelength-extended photovoltaic infrared photodetectors. Applied Physics Letters, 2014, 104, .	3.3	6
12	High temperature terahertz response in a p-type quantum dot-in-well photodetector. Applied Physics Letters, 2014, 105, 151107.	3.3	10
13	Effects of incident-light-intensity-dependent band gap narrowing on barrier heights of p-doped AlxGa1â^'xAs/GaAs heterojunction devices. Infrared Physics and Technology, 2014, 63, 193-197.	2.9	5
14	Direct observation of spin-orbit splitting and phonon-assisted optical transitions in the valence band by internal photoemission spectroscopy. Physical Review B, 2013, 88, .	3.2	6
15	InAs/GaAs p-type quantum dot infrared photodetector with higher efficiency. Applied Physics Letters, 2013, 103, .	3.3	43
16	Temperature-dependent far-infrared response of epitaxial multilayer graphene. Applied Physics Letters, 2013, 102, 231906.	3.3	6
17	Band offsets and carrier dynamics of type-II InAs/GaSb superlattice photodetectors studied by internal photoemission spectroscopy. Applied Physics Letters, 2013, 103, .	3.3	13
18	Temperature-dependent internal photoemission probe for band parameters. Physical Review B, 2012, 86, .	3.2	30

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19	Plasma frequency and dielectric function dependence on doping and temperature for p-type indium phosphide epitaxial films. Journal of Physics Condensed Matter, 2012, 24, 435803.	1.8	23
20	Design of resonant-cavity-enhanced multi-band photodetectors. Journal of Applied Physics, 2011, 110, 043112.	2.5	8
21	Effects of graded barriers on the operation of split-off band infrared detectors. Infrared Physics and Technology, 2011, 54, 296-301.	2.9	1
22	Quantum dot lasers grown by gas source molecular-beam epitaxy. Journal of Crystal Growth, 2011, 323, 450-453.	1.5	5
23	Dielectric function model for p-type semiconductor inter-valence band transitions. Journal of Applied Physics, 2011, 109, .	2.5	23
24	Analysis of Dark Current Mechanisms for Split-Off Band Infrared Detectors at High Temperatures. IEEE Transactions on Electron Devices, 2010, 57, 1230-1236.	3.0	8
25	Temperature dependence of photoluminescence from as-grown and plasma-etched InAs0.45P0.55/In0.68Ga0.32As0.45P0.55 strained single quantum well. Journal of Alloys and Compounds, 2010, 491, 595-598.	5.5	6
26	Optical Investigations of Directly Wafer-Bonded InPâ€“GaAs Heterojunctions. Journal of the Electrochemical Society, 2009, 156, H220.	2.9	4
27	InAsP/InGaAsP quantum-well 1.3â€…[micro sign]m vertical-cavity surface-emitting lasers. Electronics Letters, 2009, 45, 105.	1.0	10
28	InAs0.45P0.55/InP strained multiple quantum wells intermixed by inductively coupled plasma etching. Materials Research Bulletin, 2009, 44, 2217-2221.	5.2	2
29	Two-color quantum dot laser with tunable wavelength gap. Applied Physics Letters, 2009, 95, .	3.3	25
30	Room temperature continuous-wave operation of InAsâ•InP(100) quantum dot lasers grown by gas-source molecular-beam epitaxy. Applied Physics Letters, 2008, 93, .	3.3	43
31	Luminescence enhancement of plasma-etched InAsPâ•InGaAsP quantum wells. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 219-223.	2.1	3
32	Transparent Thin-Film Transistors Using ZnMgO as Dielectrics and Channel. IEEE Transactions on Electron Devices, 2007, 54, 2856-2859.	3.0	25
33	Cubic MgxZn1â”xO films grown on SiO2 substrates. Optical Materials, 2006, 28, 271-275.	3.6	3
34	GSMBE growth and characterizations of AlInP/InGaAsP strain-compensated multiple-layer heterostructures. Journal of Crystal Growth, 2005, 281, 255-262.	1.5	4
35	Characterization of cubic phase MgZnO/Si(100) interfaces. Applied Surface Science, 2005, 252, 1147-1152.	6.1	11
36	Luminescent properties of annealed and directly wafer-bonded InAsP/InGaAsP multiple quantum wells. Semiconductor Science and Technology, 2005, 20, 615-620.	2.0	2

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37	Observations of interfaces in direct wafer-bonded InPâ€“GaAs structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2351.	1.6	0
38	Annealing effects on the microstructure and photoluminescence properties of Ni-doped ZnO films. Applied Surface Science, 2004, 222, 263-268.	6.1	60
39	Difference of luminescent properties between strained InAsP/InP and strain-compensated InAsP/InGaAsP MQWs. Journal of Crystal Growth, 2003, 256, 96-102.	1.5	15
40	Structural and electrical properties of an Au film system deposited on silicone oil surfaces. Journal of Physics Condensed Matter, 2002, 14, 10051-10062.	1.8	19
41	Anomalous electrical conductivity of a gold thin film percolation system. Physical Review B, 2002, 66, .	3.2	19
42	Experimental observation of large ramified Au aggregates on melting glass surfaces. Physical Review B, 2001, 63, .	3.2	32